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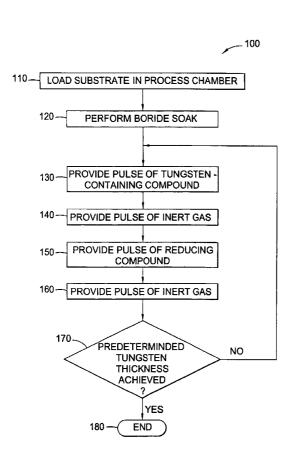
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#### (54) Title: METHOD FOR DEPOSITING METAL LAYERS EMPLOYING SEQUENTIAL DEPOSITION TECHNIQUES



(57) Abstract: A method for forming a tungsten layer on a substrate surface is provided. In one aspect, the method includes positioning the substrate surface in a processing chamber (110) and exposing the substrate surface to a boride (120). A nucleation layer is then deposited on the substrate surface in the same processing chamber by alternately pulsing a tungsten-containing compound (130) and a reducing gas (150) selected from a group consisting of silane (SiH<sub>4</sub>), disilane (Si<sub>2</sub>H<sub>6</sub>), dichlorosilane (SiCl<sub>2</sub>H<sub>2</sub>), derivatives thereof, and combinations thereof. A tungsten bulk fill may then be deposited on the nucleation layer using cyclical deposition, chemical vapor deposition, or physical vapor deposition techniques.

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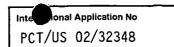
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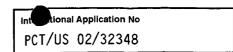
#### INTERNATIONAL SEARCH REPORT



CLASSIFICATION OF SUBJECT MATTER C 7 C23C16/455 H01L H01L21/00 C23C16/02 C23C16/06 According to International Patent Classification (IPC) or to both national classification and IPC **B. FIELDS SEARCHED** Minimum documentation searched (classification system followed by classification symbols) IPC 7 C23C Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched Electronic data base consulted during the international search (name of data base and, where practical, search terms used) EPO-Internal, PAJ C. DOCUMENTS CONSIDERED TO BE RELEVANT Relevant to claim No. Citation of document, with indication, where appropriate, of the relevant passages Category ° 1 - 20"ATOMIC LAYER DEPOSITION OF Υ YANG M ET AL: TUNGSTEN FILM FROM WF6/B2H6: NUCLEATION LAYER FOR ADVANCED SEMICONDUCTOR DEVICES" ADVANCED METALLIZATION CONFERENCE. PROCEEDINGS OF THE CONFERENCE, XX, XX, 8 October 2001 (2001-10-08), pages 655-660, XP008014661 the whole document 1 - 20US 6 156 382 A (MAEDA YUJI ET AL) Υ 5 December 2000 (2000-12-05) column 7, line 48 -column 9, line 67 1 - 20PATENT ABSTRACTS OF JAPAN Α vol. 2000, no. 16, 8 May 2001 (2001-05-08) & JP 2001 011629 A (APPLIED MATERIALS INC), 16 January 2001 (2001-01-16) abstract χ Patent family members are listed in annex. Further documents are listed in the continuation of box C. ° Special categories of cited documents: "T" later document published after the international filing date or priority date and not in conflict with the application but A<sup>\*</sup> document defining the general state of the art which is not considered to be of particular relevance cited to understand the principle or theory underlying the invention "E" earlier document but published on or after the international "X" document of particular relevance; the claimed invention filing date cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone "L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another "Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such docucitation or other special reason (as specified) document referring to an oral disclosure, use, exhibition or ments, such combination being obvious to a person skilled other means in the art. document published prior to the international filing date but later than the priority date claimed \*&\* document member of the same patent family Date of mailing of the international search report Date of the actual completion of the international search 11/04/2003 4 April 2003 Authorized officer Name and mailing address of the ISA European Patent Office, P.B. 5818 Patentlaan 2 NL – 2280 HV Rijswijk Tel. (+31–70) 340–2040, Tx. 31 651 epo nl, Fax: (+31–70) 340–3016 Ekhult, H

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Information on patent family members

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